

General Description

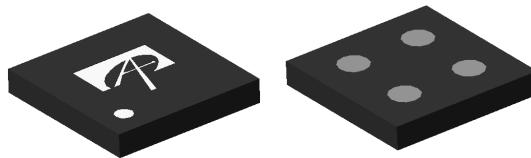
The AOC2403 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 1.5V while retaining a 8V $V_{GS(MAX)}$ rating.

Product Summary

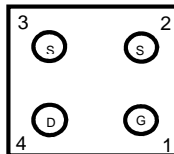
V_{DS}	-20V
I_D (at $V_{GS}=-4.5V$)	-1.8A
$R_{DS(ON)}$ (at $V_{GS}=-4.5V$)	< 95m Ω
$R_{DS(ON)}$ (at $V_{GS}=-2.5V$)	< 115m Ω
$R_{DS(ON)}$ (at $V_{GS}=-1.8V$)	< 150m Ω
$R_{DS(ON)}$ (at $V_{GS}=-1.5V$)	< 200m Ω



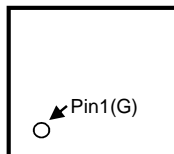
AlphaDFN 0.97x0.97_4



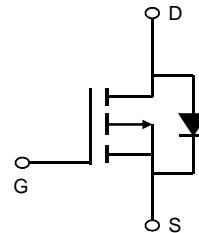
Bottom View



Top View



Equivalent Circuit



Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-20	V
Gate-Source Voltage	V_{GS}	± 8	V
Source Current (DC) ^{Note1}	I_D	-1.8	A
$T_A=25^\circ\text{C}$			
Source Current (Pulse) ^{Note2}	I_{DM}	-20	
Power Dissipation ^{Note1}	P_D	0.45	W
$T_A=25^\circ\text{C}$			
Junction and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

Note 1. Mounted on minimum pad PCB

Note 2. PW <300 μs pulses, duty cycle 0.5% max

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV _{DSS}	Source-Source Breakdown Voltage	I _D =-250μA, V _{GS} =0V	-20			V
I _{DSS}	Zero Gate Voltage Source Current	V _{DS} =-20V, V _{GS} =0V T _J =55°C			-1 -5	μA
I _{GSS}	Gate leakage current	V _{DS} =0V, V _{GS} =±8V			±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250μA	-0.3	-0.65	-1	V
R _{DS(ON)}	Static Source to Source On-Resistance	V _{GS} =-4.5V, I _D =-1A T _J =125°C		76	95	mΩ
		V _{GS} =-2.5V, I _D =-1A		91	115	
		V _{GS} =-1.8V, I _D =-0.5A		107	150	
		V _{GS} =-1.5V, I _D =-0.5A		130	200	
g _{FS}	Forward Transconductance	V _{DS} =-5V, I _D =-1A		7		S
V _{FSD}	Diode Forward Voltage	I _D =-1A, V _{GS} =0V,		-0.73	-1	V
DYNAMIC PARAMETERS						
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =-10V, f=1MHz,		405		pF
C _{oss}	Output Capacitance			75		pF
C _{rss}	Reverse Transfer Capacitance			45		pF
R _g	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz		26		Ω
SWITCHING PARAMETERS						
Q _g	Total Gate Charge	V _{GS} =-4.5V, V _{DS} =-10V, I _D =-1A		4.8		nC
Q _{gs}	Gate Source Charge			0.8		nC
Q _{gd}	Gate Drain Charge			1		nC
t _{D(on)}	Turn-On DelayTime	V _{GS} =-4.5V, V _{DS} =-10V, R _L =10Ω, I _D =-1A, R _{GEN} =6Ω		7.5		ns
t _r	Turn-On Rise Time			8.5		
t _{D(off)}	Turn-Off DelayTime			95		
t _f	Turn-Off Fall Time			30		
t _{rr}	Body Diode Reverse Recovery Time	I _F =-1A, di/dt=100A/μs		22		ns
Q _{rr}	Body Diode Reverse Recovery Charge	I _F =-1A, di/dt=100A/μs		8.5		nC

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

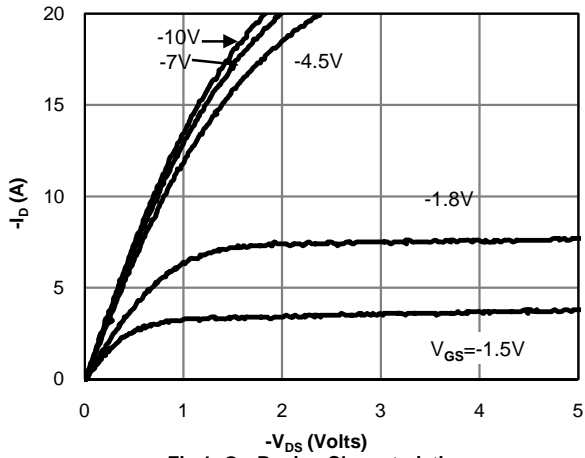


Fig 1: On-Region Characteristics

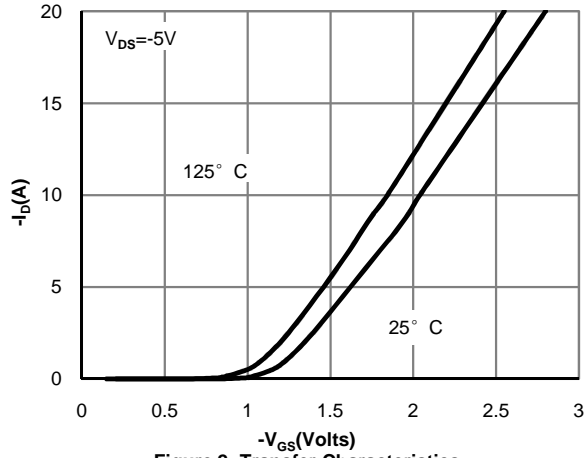


Figure 2: Transfer Characteristics

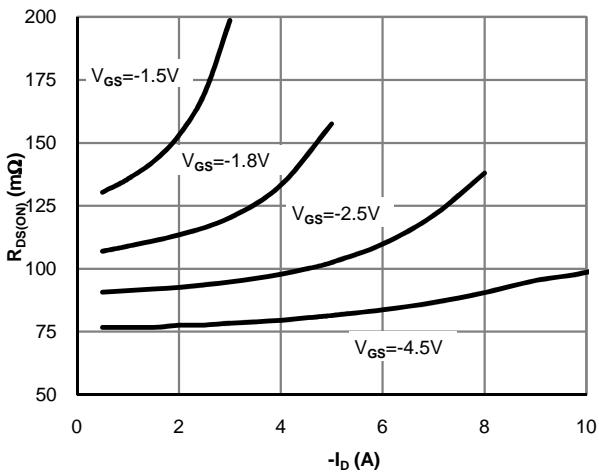


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

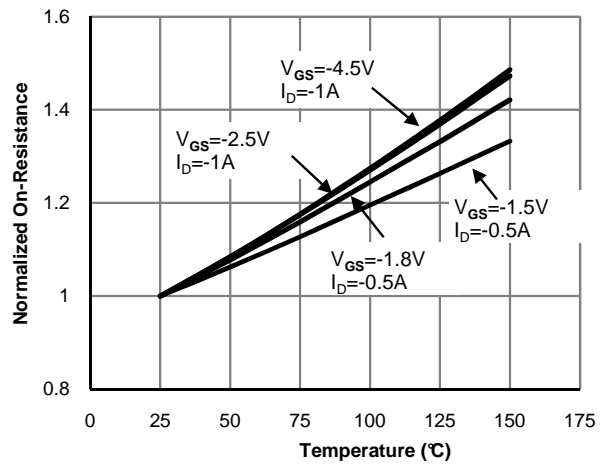


Figure 4: On-Resistance vs. Junction Temperature

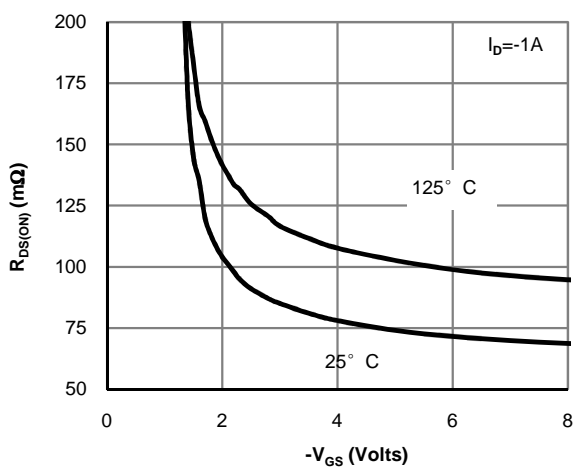


Figure 5: On-Resistance vs. Gate-Source Voltage

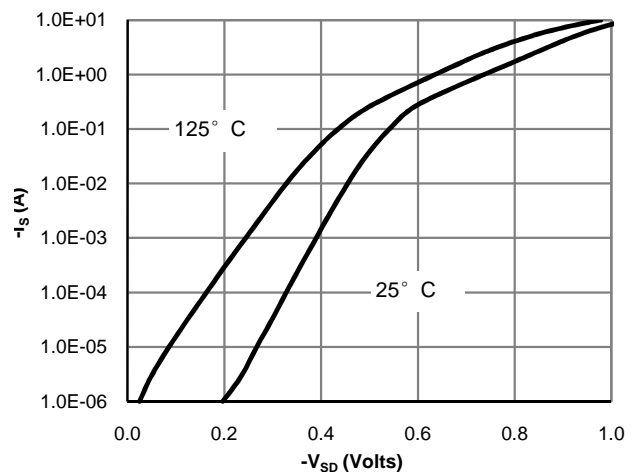


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

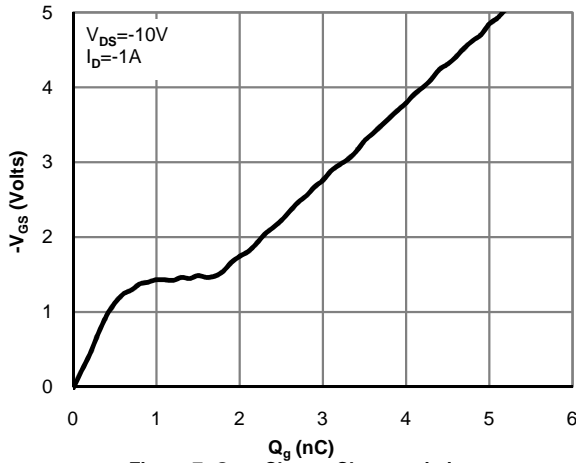


Figure 7: Gate-Charge Characteristics

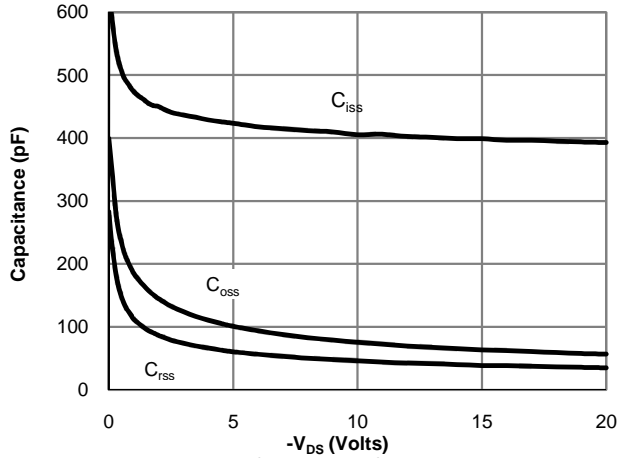


Figure 8: Capacitance Characteristics

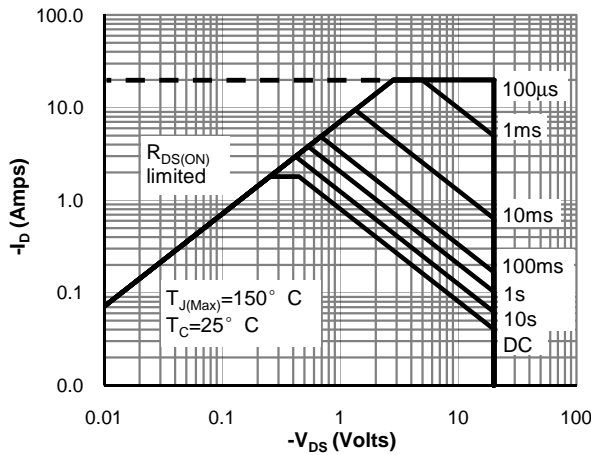


Figure 9: Maximum Forward Biased Safe Operating Area

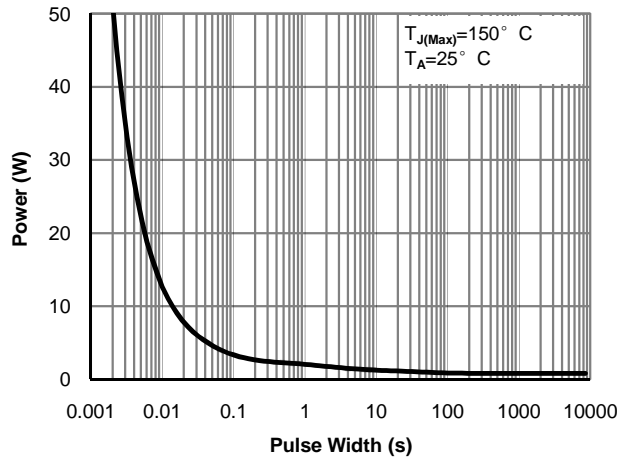


Figure 10: Single Pulse Power Rating Junction-to-Ambient

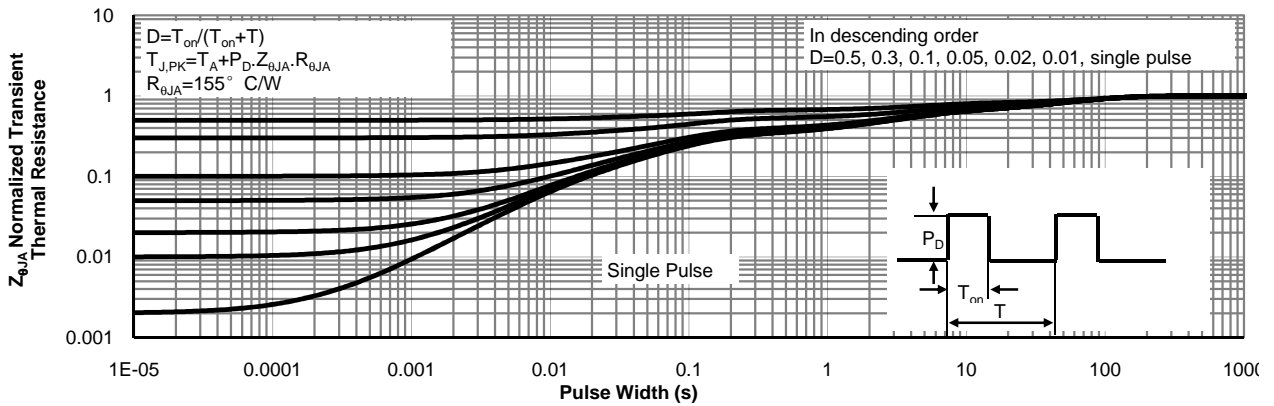


Figure 11: Normalized Maximum Transient Thermal Impedance